

**Silicon PNP Power Transistor**

**2SB1392**

**DESCRIPTION**

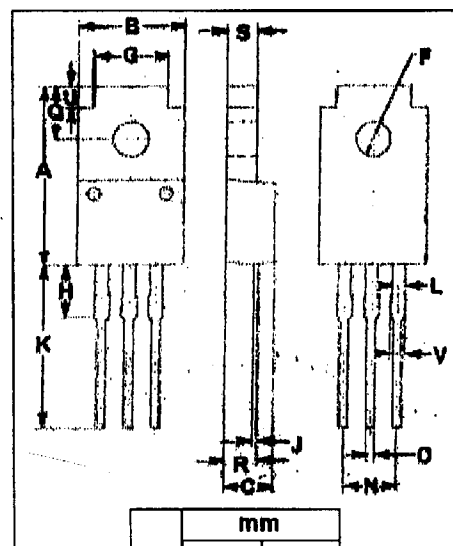
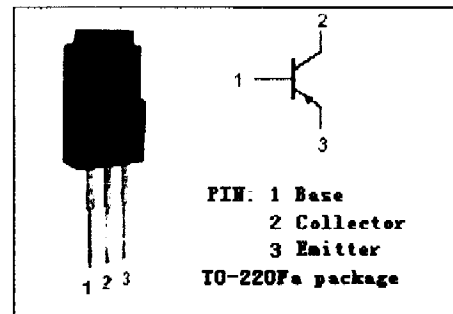
- Collector-Emitter Breakdown Voltage-  
 $V_{(BR)CEO} = -60V(\text{Min.})$
- Good Linearity of  $h_{FE}$

**APPLICATIONS**

- Designed for low frequency power amplifier applications.

**ABSOLUTE MAXIMUM RATINGS( $T_a=25^\circ\text{C}$ )**

SYMBOL	PARAMETER	VALUE	UNIT
$V_{CBO}$	Collector-Base Voltage	-70	V
$V_{CEO}$	Collector-Emitter Voltage	-60	V
$V_{EBO}$	Emitter-Base Voltage	-5	V
$I_C$	Collector Current-Continuous	-4	A
$I_{CM}$	Collector Current-Peak	-8	A
$P_C$	Collector Power Dissipation @ $T_a=25^\circ\text{C}$	2	W
	Collector Power Dissipation @ $T_c=25^\circ\text{C}$	25	
$T_J$	Junction Temperature	150	$^\circ\text{C}$
$T_{stg}$	Storage Temperature Range	-55~150	$^\circ\text{C}$



DIM	mm	
	MIN	MAX
A	16.85	17.15
B	9.54	10.10
C	4.35	4.65
D	0.75	0.90
F	3.20	3.40
G	6.90	7.20
H	5.15	5.45
J	0.45	0.75
K	13.35	13.65
L	1.10	1.30
N	4.98	5.18
Q	4.85	5.15
R	2.55	3.25
S	2.70	2.90
U	1.75	2.05
V	1.30	1.50



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## ELECTRICAL CHARACTERISTICS

$T_C=25^\circ\text{C}$  unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C = -30\text{mA}; R_{BE} = \infty$	-60			V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	$I_C = -10\mu\text{A}; I_E = 0$	-70			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E = -10\mu\text{A}; I_C = 0$	-5			V
$V_{CE(sat)*}$	Collector-Emitter Saturation Voltage	$I_C = -2\text{A}; I_B = -0.2\text{A}$			-1.0	V
$V_{BE(sat)*}$	Base-Emitter Saturation Voltage	$I_C = -2\text{A}; I_B = -0.2\text{A}$			-1.2	V
$V_{BE(on)*}$	Base-Emitter On Voltage	$I_C = -1\text{A}; V_{CE} = -4\text{V}$			-1.0	V
$I_{CBO}$	Collector Cutoff Current	$V_{CB} = -50\text{V}; I_E = 0$			-10	$\mu\text{A}$
$I_{CEO}$	Collector Cutoff Current	$V_{CE} = -50\text{V}; R_{BE} = \infty$			-10	$\mu\text{A}$
$h_{FE-1*}$	DC Current Gain	$I_C = -1\text{A}; V_{CE} = -4\text{V}$	60		200	
$h_{FE-2*}$	DC Current Gain	$I_C = -0.1\text{A}; V_{CE} = -4\text{V}$	35			

★: Pulse test

### ◆ $h_{FE-1}$ Classifications

B	C
60-120	100-200